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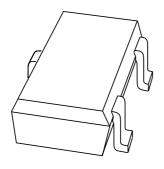
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



BAV199WLow-leakage double diode

Product data sheet Supersedes data of 1998 Jan 09 1999 May 11



Low-leakage double diode

BAV199W

FEATURES

- Small plastic SMD package
- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8 μs
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATIONS

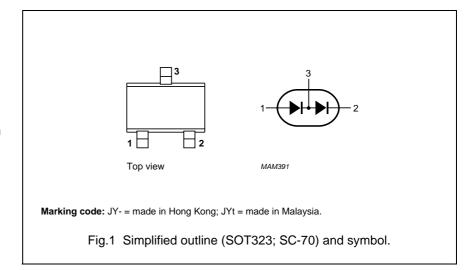
 Low-leakage current applications in surface mounted circuits.

DESCRIPTION

Epitaxial, medium-speed switching, double diode in a small plastic SOT323 (SC-70) SMD package. The diodes are connected in series.

PINNING

PIN	DESCRIPTION	
1	anode	
2	cathode	
3	cathode; anode	



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per diode unless otherwise specified						
V _{RRM}	repetitive peak reverse voltage		_	85	V	
V_R	continuous reverse voltage		_	75	V	
I _F	continuous forward current	single diode loaded; T _s = 90 °C; see Fig.2	_	135	mA	
		double diode loaded; $T_s = 90$ °C; see Fig.2	_	110	mA	
I _{FRM}	repetitive peak forward current		_	500	mA	
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4				
		$t_p = 1 \mu s$	_	4	Α	
		$t_p = 1 \text{ ms}$	_	1	Α	
		t _p = 1 s	_	0.5	Α	
P _{tot}	total power dissipation	single diode loaded; T _s = 90 °C	_	150	mW	
		double diode loaded; T _s = 90 °C	_	240	mW	
T _{stg}	storage temperature		-65	+150	°C	
Tj	junction temperature		_	150	°C	

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Low-leakage double diode

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ELECTRICAL CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
Per diode					
V _F	forward voltage	see Fig.3			
		I _F = 1 mA	_	900	mV
		I _F = 10 mA	_	1000	mV
		I _F = 50 mA	_	1100	mV
		I _F = 150 mA	_	1250	mV
I _R	reverse current	see Fig.5			
		V _R = 75 V	0.003	5	nA
		V _R = 75 V; T _j = 150 °C	3	80	nA
C _d	diode capacitance	f = 1 MHz; V _R = 0; see Fig.6	2	_	pF
t _{rr}	reverse recovery time	when switched from I _F = 10 mA to	0.8	3	μs
		I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.7			

THERMAL CHARACTERISTICS

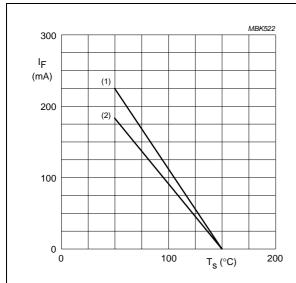
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-s}	thermal resistance from junction to soldering point	T _s = 90 °C	400	K/W

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Low-leakage double diode

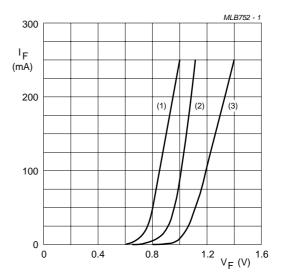
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GRAPHICAL DATA



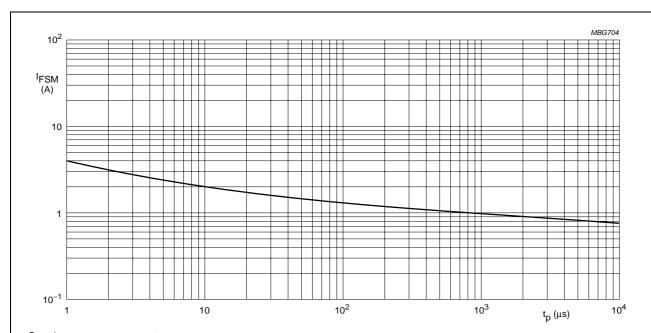
- (1) Single diode loaded.
- (2) Double diodes loaded.

Fig.2 Maximum permissible continuous forward current as a function of soldering point temperature; per diode.



- (1) T_i = 150 °C; typical values.
- (2) $T_i = 25$ °C; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage; per diode.



Based on square wave currents. $T_i = 25$ °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration per diode.

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Low-leakage double diode

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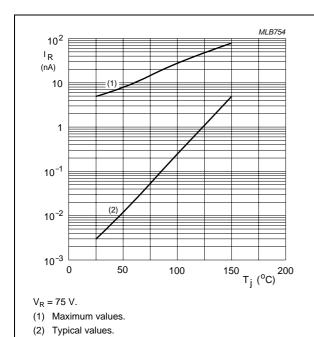
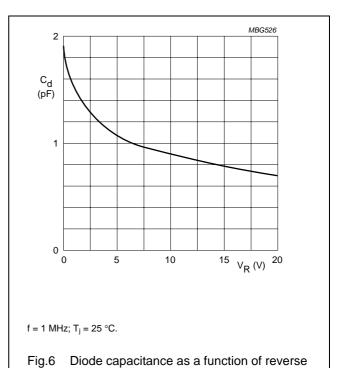
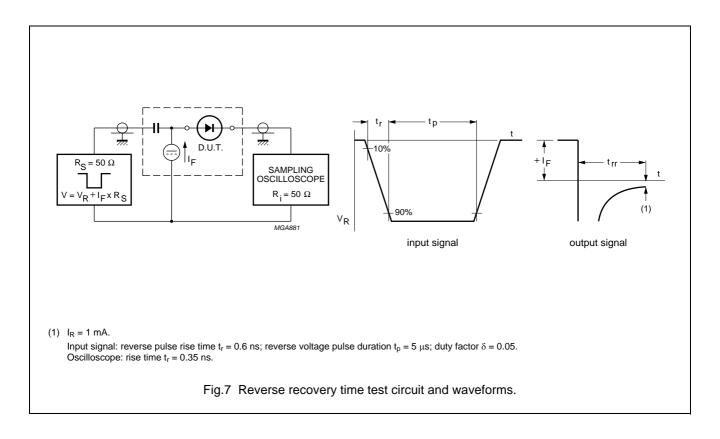


Fig.5 Reverse current as a function of junction temperature; per diode.



voltage; per diode; typical values.



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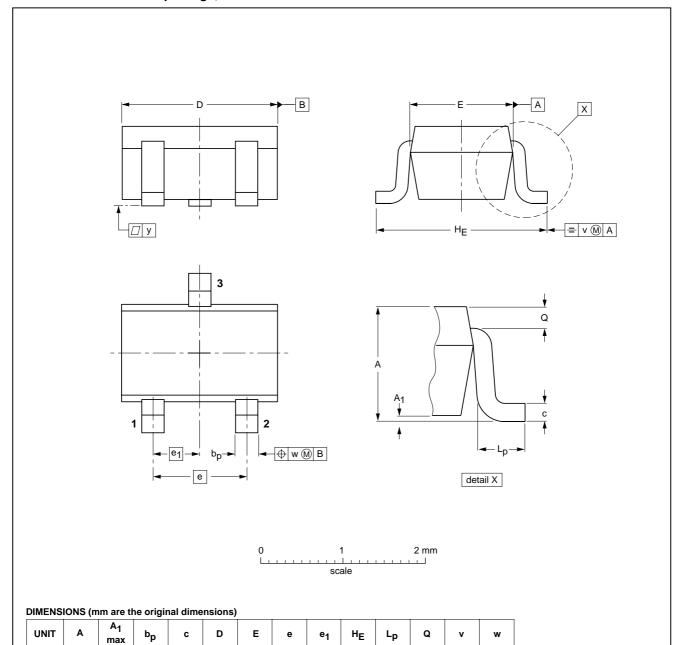
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION 1850E DA	
SOT323			SC-70			97-02-28

1.3

0.65

0.45

0.2

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0.4

mm

0.25

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

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Contact information

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 Printed in The Netherlands
 115002/00/03/pp8
 Date of release: 1999 May 11
 Document order number: 9397 750 05947

